

Jean-Pierre Raskin

List of Publications by Year in descending order

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364
papers

8,056
citations

53660

45
h-index

88477

70
g-index

366
all docs

366
docs citations

366
times ranked

5817
citing authors

#	ARTICLE	IF	CITATIONS
1	Substrate crosstalk reduction using SOI technology. IEEE Transactions on Electron Devices, 1997, 44, 2252-2261.	1.6	251
2	Raman and XPS characterization of vanadium oxide thin films with temperature. Applied Surface Science, 2017, 403, 717-727.	3.1	216
3	Influence of device engineering on the analog and RF performances of SOI MOSFETs. IEEE Transactions on Electron Devices, 2003, 50, 577-588.	1.6	195
4	Analog/RF performance of multiple gate SOI devices: wideband simulations and characterization. IEEE Transactions on Electron Devices, 2006, 53, 1088-1095.	1.6	156
5	FinFET analogue characterization from DC to 110GHz. Solid-State Electronics, 2005, 49, 1488-1496.	0.8	142
6	RF Extraction of Self-Heating Effects in FinFETs. IEEE Transactions on Electron Devices, 2011, 58, 3335-3341.	1.6	138
7	A comprehensive review on microwave FinFET modeling for progressing beyond the state of art. Solid-State Electronics, 2013, 80, 81-95.	0.8	121
8	Accurate SOI MOSFET characterization at microwave frequencies for device performance optimization and analog modeling. IEEE Transactions on Electron Devices, 1998, 45, 1017-1025.	1.6	120
9	New substrate passivation method dedicated to HR SOI wafer fabrication with increased substrate resistivity. IEEE Electron Device Letters, 2005, 26, 805-807.	2.2	116
10	What are the limiting parameters of deep-submicron MOSFETs for high frequency applications?. IEEE Electron Device Letters, 2003, 24, 189-191.	2.2	107
11	Effective resistivity of fully-processed SOI substrates. Solid-State Electronics, 2005, 49, 491-496.	0.8	106
12	Inter- and intragranular plasticity mechanisms in ultrafine-grained Al thin films: An in situ TEM study. Acta Materialia, 2013, 61, 205-216.	3.8	106
13	High-Frequency Noise Performance of 60-nm Gate-Length FinFETs. IEEE Transactions on Electron Devices, 2008, 55, 2718-2727.	1.6	104
14	Substrate loss mechanisms for microstrip and CPW transmission lines on lossy silicon wafers. Solid-State Electronics, 2003, 47, 1927-1936.	0.8	103
15	New On-Chip Nanomechanical Testing Laboratory - Applications to Aluminum and Polysilicon Thin Films. Journal of Microelectromechanical Systems, 2009, 18, 555-569.	1.7	102
16	Impact of Extrinsic Capacitances on FinFET RF Performance. IEEE Transactions on Microwave Theory and Techniques, 2013, 61, 833-840.	2.9	100
17	Parasitic Gate Capacitance Model for Triple-Gate FinFETs. IEEE Transactions on Electron Devices, 2013, 60, 3710-3717.	1.6	100
18	Laterally asymmetric channel engineering in fully depleted double gate SOI MOSFETs for high performance analog applications. Solid-State Electronics, 2004, 48, 947-959.	0.8	95

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19	Low-temperature wafer bonding: a study of void formation and influence on bonding strength. <i>Journal of Microelectromechanical Systems</i> , 2005, 14, 368-382.	1.7	92
20	RF Harmonic Distortion of CPW Lines on HR-Si and Trap-Rich HR-Si Substrates. <i>IEEE Transactions on Electron Devices</i> , 2012, 59, 924-932.	1.6	92
21	Extrinsic mechanical size effects in thin ZrNi metallic glass films. <i>Acta Materialia</i> , 2015, 90, 232-241.	3.8	89
22	Raman scattering study of the phonon dispersion in twisted bilayer graphene. <i>Nano Research</i> , 2013, 6, 269-274.	5.8	85
23	Fully depleted SOI CMOS technology for heterogeneous micropower, high-temperature or RF microsystems. <i>Solid-State Electronics</i> , 2001, 45, 541-549.	0.8	81
24	Thin films stress extraction using micromachined structures and wafer curvature measurements. <i>Microelectronic Engineering</i> , 2004, 76, 219-226.	1.1	73
25	Homogeneous flow and size dependent mechanical behavior in highly ductile Zr65Ni35 metallic glass films. <i>Acta Materialia</i> , 2017, 131, 246-259.	3.8	72
26	Electrical detection of DNA hybridization: Three extraction techniques based on interdigitated Al/Al ₂ O ₃ capacitors. <i>Biosensors and Bioelectronics</i> , 2007, 22, 2199-2207.	5.3	66
27	An ammonia sensor composed of polypyrrole synthesized on reduced graphene oxide by electropolymerization. <i>Sensors and Actuators B: Chemical</i> , 2020, 305, 127423.	4.0	64
28	High-frequency four noise parameters of silicon-on-insulator-based technology MOSFET for the design of low-noise RF integrated circuits. <i>IEEE Transactions on Electron Devices</i> , 1999, 46, 1733-1741.	1.6	61
29	Role of Cu foil in-situ annealing in controlling the size and thickness of CVD graphene domains. <i>Carbon</i> , 2018, 129, 270-280.	5.4	61
30	A Review on Functionalized Graphene Sensors for Detection of Ammonia. <i>Sensors</i> , 2021, 21, 1443.	2.1	61
31	SOI CMOS Compatible Low-Power Microheater Optimization for the Fabrication of Smart Gas Sensors. <i>IEEE Sensors Journal</i> , 2004, 4, 670-680.	2.4	58
32	Chemically deposited palladium nanoparticles on graphene for hydrogen sensor applications. <i>Scientific Reports</i> , 2019, 9, 3653.	1.6	57
33	A novel parametric-effect MEMS amplifier. <i>Journal of Microelectromechanical Systems</i> , 2000, 9, 528-537.	1.7	56
34	RF Performance of a Commercial SOI Technology Transferred Onto a Passivated HR Silicon Substrate. <i>IEEE Transactions on Electron Devices</i> , 2008, 55, 1664-1671.	1.6	55
35	A Formaldehyde Sensor Based on Molecularly-Imprinted Polymer on a TiO ₂ Nanotube Array. <i>Sensors</i> , 2017, 17, 675.	2.1	55
36	Compact model for highly-doped double-gate SOI MOSFETs targeting baseband analog applications. <i>Solid-State Electronics</i> , 2007, 51, 655-661.	0.8	54

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37	Dislocation-mediated relaxation in nanograined columnar palladium films revealed by on-chip time-resolved HRTEM testing. <i>Nature Communications</i> , 2015, 6, 5922.	5.8	53
38	High strength-ductility of thin nanocrystalline palladium films with nanoscale twins: On-chip testing and grain aggregate model. <i>Acta Materialia</i> , 2012, 60, 1795-1806.	3.8	52
39	Mode conversion at GCPW-to-microstrip-line transitions. <i>IEEE Transactions on Microwave Theory and Techniques</i> , 2000, 48, 158-161.	2.9	51
40	Ultra-thin body and thin-BOX SOI CMOS technology analog figures of merit. <i>Solid-State Electronics</i> , 2012, 70, 50-58.	0.8	50
41	On the MOSFET Threshold Voltage Extraction by Transconductance and Transconductance-to-Current Ratio Change Methods: Part II – Effect of Drain Voltage. <i>IEEE Transactions on Electron Devices</i> , 2011, 58, 4180-4188.	1.6	49
42	RF Performance of SOI CMOS Technology on Commercial 200-mm Enhanced Signal Integrity High Resistivity SOI Substrate. <i>IEEE Transactions on Electron Devices</i> , 2014, 61, 722-728.	1.6	49
43	On the MOSFET Threshold Voltage Extraction by Transconductance and Transconductance-to-Current Ratio Change Methods: Part I – Effect of Gate-Voltage-Dependent Mobility. <i>IEEE Transactions on Electron Devices</i> , 2011, 58, 4172-4179.	1.6	48
44	Time and Frequency Domain Characterization of Transistor Self-Heating. <i>IEEE Transactions on Electron Devices</i> , 2013, 60, 1844-1851.	1.6	47
45	Impact of self-heating and substrate effects on small-signal output conductance in UTBB SOI MOSFETs. <i>Solid-State Electronics</i> , 2012, 71, 93-100.	0.8	46
46	Floating effective back-gate effect on the small-signal output conductance of SOI MOSFETs. <i>IEEE Electron Device Letters</i> , 2003, 24, 414-416.	2.2	45
47	Assessment of 28 nm UTBB FD-SOI technology platform for RF applications: Figures of merit and effect of parasitic elements. <i>Solid-State Electronics</i> , 2016, 117, 130-137.	0.8	45
48	UTBB SOI MOSFETs analog figures of merit: Effects of ground plane and asymmetric double-gate regime. <i>Solid-State Electronics</i> , 2013, 90, 56-64.	0.8	44
49	CVD synthesis of mono- and few-layer graphene using alcohols at low hydrogen concentration and atmospheric pressure. <i>Chemical Physics Letters</i> , 2013, 584, 142-146.	1.2	43
50	Substrate impact on threshold voltage and subthreshold slope of sub-32 nm ultra thin SOI MOSFETs with thin buried oxide and undoped channel. <i>Solid-State Electronics</i> , 2010, 54, 213-219.	0.8	42
51	Direct protein detection with a nano-interdigitated array gate MOSFET. <i>Biosensors and Bioelectronics</i> , 2009, 24, 3531-3537.	5.3	40
52	A new interdigitated array microelectrode-oxide-silicon sensor with label-free, high sensitivity and specificity for fast bacteria detection. <i>Sensors and Actuators B: Chemical</i> , 2011, 156, 578-587.	4.0	40
53	Fundamental limitations in transferred CVD graphene caused by Cu catalyst surface morphology. <i>Carbon</i> , 2020, 163, 95-104.	5.4	40
54	A Fast and Room-Temperature Operation Ammonia Sensor Based on Compound of Graphene With Polypyrrole. <i>IEEE Sensors Journal</i> , 2018, 18, 9088-9096.	2.4	39

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55	Internal stress relaxation based method for elastic stiffness characterization of very thin films. Thin Solid Films, 2009, 518, 260-264.	0.8	38
56	Mobility improvement in nanowire junctionless transistors by uniaxial strain. Applied Physics Letters, 2010, 97, .	1.5	38
57	On-chip tensile testing of nanoscale silicon free-standing beams. Journal of Materials Research, 2012, 27, 571-579.	1.2	37
58	Extended MASTAR Modeling of DIBL in UTB and UTBB SOI MOSFETs. IEEE Transactions on Electron Devices, 2012, 59, 247-251.	1.6	36
59	RF MEMS Passives on High-Resistivity Silicon Substrates. IEEE Microwave and Wireless Components Letters, 2013, 23, 632-634.	2.0	36
60	Compositional-induced structural change in Zr _x Ni _{100-x} thin film metallic glasses. Journal of Alloys and Compounds, 2014, 615, S348-S351.	2.8	36
61	Effect of parasitic elements on UTBB FD SOI MOSFETs RF figures of merit. Solid-State Electronics, 2014, 97, 38-44.	0.8	36
62	Design of a Novel MEMS Microgripper with Rotatory Electrostatic Comb-Drive Actuators for Biomedical Applications. Sensors, 2018, 18, 1664.	2.1	35
63	Analysis of Static and Dynamic Performance of Short-Channel Double-Gate Silicon-on-Insulator Metal-Oxide-Semiconductor Field-Effect Transistors for Improved Cutoff Frequency. Japanese Journal of Applied Physics, 2005, 44, 2340-2346.	0.8	34
64	Planar double-gate SOI MOS devices: Fabrication by wafer bonding over pre-patterned cavities and electrical characterization. Solid-State Electronics, 2007, 51, 231-238.	0.8	34
65	RF Small-Signal Analysis of Schottky-Barrier p-MOSFET. IEEE Transactions on Electron Devices, 2008, 55, 1192-1202.	1.6	34
66	Experimental study of transconductance and mobility behaviors in ultra-thin SOI MOSFETs with standard and thin buried oxides. Solid-State Electronics, 2010, 54, 164-170.	0.8	34
67	Size-dependent failure mechanisms in ZrNi thin metallic glass films. Scripta Materialia, 2014, 89, 9-12.	2.6	34
68	Pressure-Controlled Chemical Vapor Deposition of Single-Layer Graphene with Millimeter-Size Domains on Thin Copper Film. Chemistry of Materials, 2017, 29, 3431-3440.	3.2	34
69	Noise modeling in fully depleted SOI MOSFETs. Solid-State Electronics, 2004, 48, 813-825.	0.8	33
70	Perspective of FinFETs for analog applications. , 0, , .		33
71	Ultrawide Frequency Range Crosstalk Into Standard and Trap-Rich High Resistivity Silicon Substrates. IEEE Transactions on Electron Devices, 2011, 58, 4258-4264.	1.6	33
72	On-chip stress relaxation testing method for freestanding thin film materials. Review of Scientific Instruments, 2012, 83, 105004.	0.6	33

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73	Raman measurements of uniaxial strain in silicon nanostructures. Journal of Applied Physics, 2013, 114, .	1.1	33
74	Electrical characterization of true Silicon-On-Nothing MOSFETs fabricated by Si layer transfer over a pre-etched cavity. Solid-State Electronics, 2007, 51, 1238-1244.	0.8	32
75	Point Defect Clusters and Dislocations in FIB Irradiated Nanocrystalline Aluminum Films: An Electron Tomography and Aberration-Corrected High-Resolution ADF-STEM Study. Microscopy and Microanalysis, 2011, 17, 983-990.	0.2	32
76	Plasticity mechanisms in ultrafine grained freestanding aluminum thin films revealed by <i>in-situ</i> transmission electron microscopy nanomechanical testing. Applied Physics Letters, 2014, 104, .	1.5	32
77	Damage evaluation in graphene underlying atomic layer deposition dielectrics. Scientific Reports, 2015, 5, 13523.	1.6	32
78	Novel class of nanostructured metallic glass films with superior and tunable mechanical properties. Acta Materialia, 2021, 213, 116955.	3.8	32
79	Electrical characteristics and simulations of self-switching-diodes in SOI technology. Solid-State Electronics, 2007, 51, 1245-1249.	0.8	31
80	Review on analog/radio frequency performance of advanced silicon MOSFETs. Semiconductor Science and Technology, 2017, 32, 123004.	1.0	31
81	Microfabrication-based nanomechanical laboratory for testing the ductility of submicron aluminium films. Microelectronic Engineering, 2007, 84, 2714-2718.	1.1	30
82	Twisted Bilayer Graphene: Microscopic Rainbows. Small, 2013, 9, 3247-3251.	5.2	30
83	Wide frequency band assessment of 28nm FDSOI technology platform for analogue and RF applications. Solid-State Electronics, 2015, 108, 47-52.	0.8	29
84	Porous silicon membranes and their applications: Recent advances. Sensors and Actuators A: Physical, 2021, 318, 112486.	2.0	29
85	Impact of Downscaling on High-Frequency Noise Performance of Bulk and SOI MOSFETs. IEEE Transactions on Electron Devices, 2004, 51, 1605-1612.	1.6	28
86	Detection mechanism in highly sensitive ZnO nanowires network gas sensors. Sensors and Actuators B: Chemical, 2019, 297, 126602.	4.0	28
87	High-temperature DC and RF behaviors of partially-depleted SOI MOSFET transistors. Solid-State Electronics, 2008, 52, 1924-1932.	0.8	27
88	Advanced Si-based substrates for RF passive integration: Comparison between local porous Si layer technology and trap-rich high resistivity Si. Solid-State Electronics, 2013, 87, 27-33.	0.8	27
89	28-nm FD-SOI CMOS RF Figures of Merit Down to 4.2 K. IEEE Journal of the Electron Devices Society, 2020, 8, 646-654.	1.2	27
90	Harmonic distortion analysis of double gate graded-channel MOSFETs operating in saturation. Microelectronics Journal, 2008, 39, 1663-1670.	1.1	26

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91	An asymmetric channel SOI nMOSFET for improving DC and microwave characteristics. Solid-State Electronics, 2002, 46, 1005-1011.	0.8	25
92	Analysis of quasi double gate method for performance prediction of deep submicron double gate SOI MOSFETs. Semiconductor Science and Technology, 2005, 20, 423-429.	1.0	25
93	Optimization of RF Performance of Metallic Source/Drain SOI MOSFETs Using Dopant Segregation at the Schottky Interface. IEEE Electron Device Letters, 2009, 30, 1197-1199.	2.2	25
94	Exploring the mechanical size effects in Zr65Ni35 thin film metallic glasses. Journal of Alloys and Compounds, 2014, 615, S90-S92.	2.8	25
95	Frequency Variation of the Small-Signal Output Conductance of Decanometer MOSFETs Due to Substrate Crosstalk. IEEE Electron Device Letters, 2007, 28, 419-421.	2.2	24
96	Experimental Investigation of RF Noise Performance Improvement in Graded-Channel MOSFETs. IEEE Transactions on Electron Devices, 2009, 56, 1516-1522.	1.6	24
97	Direct growth of graphitic carbon on Si(111). Applied Physics Letters, 2013, 102, .	1.5	24
98	Role of the Cu substrate in the growth of ultra-flat crack-free highly-crystalline single-layer graphene. Nanoscale, 2018, 10, 21898-21909.	2.8	24
99	Probing carrier concentration in gated single, bi- and tri-layer CVD graphene using Raman spectroscopy. Carbon, 2019, 149, 390-399.	5.4	24
100	A 140-170-GHz low-noise uniplanar subharmonic Schottky receiver. IEEE Transactions on Microwave Theory and Techniques, 2000, 48, 1416-1419.	2.9	23
101	A Simple Method for Measuring Si-Fin Sidewall Roughness by AFM. IEEE Nanotechnology Magazine, 2009, 8, 611-616.	1.1	23
102	Radio-Frequency Study of Dopant-Segregated n-Type SB-MOSFETs on Thin-Body SOI. IEEE Electron Device Letters, 2010, 31, 537-539.	2.2	23
103	High-Throughput On-Chip Large Deformation of Silicon Nanoribbons and Nanowires. Journal of Microelectromechanical Systems, 2012, 21, 822-829.	1.7	23
104	A MEMS-based magnetic field sensor with simple resonant structure and linear electrical response. Microelectronic Engineering, 2015, 142, 12-21.	1.1	23
105	Low-Loss Si-Substrates Enhanced Using Buried PN Junctions for RF Applications. IEEE Electron Device Letters, 2019, 40, 690-693.	2.2	23
106	Accurate effective mobility extraction by split C-V technique in SOI MOSFETs: suppression of the influence of floating-body effects. IEEE Electron Device Letters, 2005, 26, 749-751.	2.2	22
107	Three-Dimensional Self-Assembled Sensors in Thin-Film SOI Technology. Journal of Microelectromechanical Systems, 2006, 15, 1687-1697.	1.7	22
108	Silicon-on-Nothing MOSFETs: An efficient solution for parasitic substrate coupling suppression in SOI devices. Applied Surface Science, 2008, 254, 6168-6173.	3.1	22

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109	Strain gradient plasticity analysis of the strength and ductility of thin metallic films using an enriched interface model. <i>Acta Materialia</i> , 2010, 58, 4940-4949.	3.8	22
110	Energy-Band Engineering for Improved Charge Retention in Fully Self-Aligned Double Floating-Gate Single-Electron Memories. <i>Nano Letters</i> , 2011, 11, 4520-4526.	4.5	22
111	Automated Design of a 13.56 MHz 19 μ W Passive Rectifier With 72% Efficiency Under 10 μ A load. <i>IEEE Journal of Solid-State Circuits</i> , 2016, 51, 1290-1301.	3.5	22
112	Defect-free functionalized graphene sensor for formaldehyde detection. <i>Nanotechnology</i> , 2017, 28, 055501.	1.3	22
113	W-band single-layer vertical transitions. <i>IEEE Transactions on Microwave Theory and Techniques</i> , 2000, 48, 161-164.	2.9	21
114	High Gain and Fast Detection of Warfare Agents Using Back-Gated Silicon-Nanowired MOSFETs. <i>IEEE Electron Device Letters</i> , 2011, 32, 976-978.	2.2	21
115	Piezoresistance of nano-scale silicon up to 2%GPa in tension. <i>Applied Physics Letters</i> , 2013, 102, .	1.5	21
116	Out-of-plane MEMS-based mechanical airflow sensor co-integrated in SOI CMOS technology. <i>Sensors and Actuators A: Physical</i> , 2014, 206, 67-74.	2.0	21
117	Direct growth of graphene on Si(111). <i>Journal of Applied Physics</i> , 2014, 115, 223704.	1.1	21
118	Comparison of self-heating and its effect on analogue performance in 28 nm bulk and FDSOI. <i>Solid-State Electronics</i> , 2016, 115, 219-224.	0.8	21
119	28 μ m FDSOI analog and RF Figures of Merit at N2 cryogenic temperatures. <i>Solid-State Electronics</i> , 2019, 159, 77-82.	0.8	21
120	0.25 μ m fully depleted SOI MOSFETs for RF mixed analog-digital circuits, including a comparison with partially depleted devices with relation to high frequency noise parameters. <i>Solid-State Electronics</i> , 2002, 46, 379-386.	0.8	20
121	Low Schottky barrier height for ErSi $_{2-x}$ /n-Si contacts formed with a Ti cap. <i>Journal of Applied Physics</i> , 2008, 104, 103523.	1.1	20
122	Effect of geometrical nonlinearity on MEMS thermoelastic damping. <i>Nonlinear Analysis: Real World Applications</i> , 2009, 10, 1579-1588.	0.9	20
123	Mechanical behavior of ultrathin sputter deposited porous amorphous Al $_2$ O $_3$ films. <i>Acta Materialia</i> , 2017, 125, 27-37.	3.8	20
124	(Invited) SOI Technologies for RF and Millimeter Wave Applications. <i>ECS Transactions</i> , 2019, 92, 79-94.	0.3	20
125	Potential and modeling of 1 μ m SOI CMOS operational transconductance amplifiers for applications up to 1 GHz. <i>IEEE Journal of Solid-State Circuits</i> , 1998, 33, 640-643.	3.5	19
126	Low-Temperature Wafer Bonding. <i>Electrochemical and Solid-State Letters</i> , 2004, 7, G172.	2.2	19

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127	Low-cost optical instrumentation for thermal characterization of MEMS. Measurement Science and Technology, 2005, 16, 1833-1840.	1.4	19
128	Optimizing FinFET geometry and parasitics for RF applications. , 2008, , .		19
129	Schottky barrier lowering with the formation of crystalline Er silicide on n-Si upon thermal annealing. Applied Physics Letters, 2009, 94, 191913.	1.5	19
130	Strain in silicon nanowire beams. Journal of Applied Physics, 2012, 112, .	1.1	19
131	On-chip fracture testing of freestanding nanoscale materials. Engineering Fracture Mechanics, 2015, 150, 222-238.	2.0	19
132	A SPDT RF Switch Small- and Large-Signal Characteristics on TR-HR SOI Substrates. IEEE Journal of the Electron Devices Society, 2018, 6, 543-550.	1.2	19
133	Small- and Large-Signal Performance Up To 175 Å°C of Low-Cost Porous Silicon Substrate for RF Applications. IEEE Transactions on Electron Devices, 2018, 65, 1887-1895.	1.6	19
134	MEMS-based microstructures for nanomechanical characterization of thin films. Smart Materials and Structures, 2009, 18, 115018.	1.8	18
135	FinFET and UTBB for RF SOI communication systems. Solid-State Electronics, 2016, 125, 73-81.	0.8	18
136	A microscopic interpretation of the RF noise performance of fabricated FDSOI MOSFETs. IEEE Transactions on Electron Devices, 2006, 53, 523-532.	1.6	17
137	A 2.4-GHz Fully Integrated ESD-Protected Low-Noise Amplifier in 130-nm PD SOI CMOS Technology. IEEE Transactions on Microwave Theory and Techniques, 2007, 55, 2822-2831.	2.9	17
138	A 7-dB 43-GHz CMOS Distributed Amplifier on High-Resistivity SOI Substrates. IEEE Transactions on Microwave Theory and Techniques, 2008, 56, 587-598.	2.9	17
139	On the gm/ID-based approaches for threshold voltage extraction in advanced MOSFETs and their application to ultra-thin body SOI MOSFETs. Solid-State Electronics, 2014, 97, 52-58.	0.8	17
140	Siliconâ€onâ€insulator MOSFETs models in analog/RF domain. International Journal of Numerical Modelling: Electronic Networks, Devices and Fields, 2014, 27, 707-735.	1.2	17
141	Adhesionless and near-ideal contact behavior of graphene on Cu thin film. Carbon, 2017, 122, 446-450.	5.4	17
142	Effect of interfacial SiO2 thickness for low temperature O2 plasma activated wafer bonding. Microsystem Technologies, 2006, 12, 383-390.	1.2	16
143	Etch Rate Modification of SiO[sub 2] by Ion Damage. Electrochemical and Solid-State Letters, 2006, 9, G245.	2.2	16
144	Bulk and surface micromachined MEMS in thin film SOI technology. Electrochimica Acta, 2007, 52, 2850-2861.	2.6	16

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145	The impact of etched trenches geometry and dielectric material on the electrical behaviour of silicon-on-insulator self-switching diodes. <i>Nanotechnology</i> , 2011, 22, 435203.	1.3	16
146	Wide frequency band assessment of 28 nm FDSOI technology platform for analogue and RF applications. , 2014, , .		16
147	Design and Modeling of a MEMS Dual-Backplate Capacitive Microphone with Spring-Supported Diaphragm for Mobile Device Applications. <i>Sensors</i> , 2018, 18, 3545.	2.1	16
148	Multi-wafer batch synthesis of graphene on Cu films by quasi-static flow chemical vapor deposition. <i>2D Materials</i> , 2019, 6, 045032.	2.0	16
149	Modeling of Semiconductor Substrates for RF Applications: Part I—Static and Dynamic Physics of Carriers and Traps. <i>IEEE Transactions on Electron Devices</i> , 2021, 68, 4598-4605.	1.6	16
150	Characterization of ultrathin SOI film and application to short channel MOSFETs. <i>Nanotechnology</i> , 2008, 19, 165703.	1.3	15
151	On extraction of self-heating features in UTBB SOI MOSFETs. , 2012, , .		15
152	RF and linear performance of commercial 200 mm trap-rich HR-SOI wafers for SoC applications. , 2013, , .		15
153	Trigate nanowire MOSFETs analog figures of merit. <i>Solid-State Electronics</i> , 2015, 112, 78-84.	0.8	15
154	Determining the reference impedance of on-wafer TLR calibrations on lossy substrates. , 1996, , .		14
155	High frequency degradation of body-contacted PD SOI MOSFET output conductance. <i>Semiconductor Science and Technology</i> , 2005, 20, 469-472.	1.0	14
156	High performance analog operation of double gate transistors with the graded-channel architecture at low temperatures. <i>Solid-State Electronics</i> , 2005, 49, 1569-1575.	0.8	14
157	Characterization of FD SOI devices and VCOs on thin dielectric membranes under pressure. <i>Solid-State Electronics</i> , 2007, 51, 1229-1237.	0.8	14
158	Impact of Si substrate resistivity on the non-linear behaviour of RF CPW transmission lines. , 2008, , .		14
159	Multiscale modelling framework for the fracture of thin brittle polycrystalline films: application to polysilicon. <i>Computational Mechanics</i> , 2015, 55, 73-91.	2.2	14
160	SOI technology pushes the limits of CMOS for RF applications. , 2016, , .		14
161	Post-process porous silicon for 5G applications. <i>Solid-State Electronics</i> , 2020, 168, 107719.	0.8	14
162	Surface states and conductivity of silicon nano-wires. <i>Journal of Applied Physics</i> , 2013, 113, 134502.	1.1	13

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163	Effect of temperature on advanced Si-based substrates performance for RF passive integration. <i>Microelectronic Engineering</i> , 2014, 120, 205-209.	1.1	13
164	Mechanical characterization and modelling of Lorentz force based MEMS magnetic field sensors. <i>Solid-State Electronics</i> , 2015, 112, 68-77.	0.8	13
165	A novel on chip test method to characterize the creep behavior of metallic layers under heavy ion irradiation. <i>Journal of Nuclear Materials</i> , 2016, 476, 20-29.	1.3	13
166	Size dependent fracture strength and cracking mechanisms in freestanding polycrystalline silicon films with nanoscale thickness. <i>Engineering Fracture Mechanics</i> , 2016, 168, 190-203.	2.0	13
167	A versatile lab-on-chip test platform to characterize elementary deformation mechanisms and electromechanical couplings in nanoscopic objects. <i>Comptes Rendus Physique</i> , 2016, 17, 485-495.	0.3	13
168	RF SOI CMOS technology on 1st and 2nd generation trap-rich high resistivity SOI wafers. <i>Solid-State Electronics</i> , 2017, 128, 121-128.	0.8	13
169	Atomic-scale viscoplasticity mechanisms revealed in high ductility metallic glass films. <i>Scientific Reports</i> , 2019, 9, 13426.	1.6	13
170	Opto-electrical properties and internal stress in Al:ZnO thin films deposited by direct current reactive sputtering. <i>Thin Solid Films</i> , 2020, 695, 137760.	0.8	13
171	Intelligent SOI CMOS integrated circuits and sensors for heterogeneous environments and applications. , 0, , .		12
172	AC Behavior of Gate-Induced Floating Body Effects in Ultrathin Oxide PD SOI MOSFETs. <i>IEEE Electron Device Letters</i> , 2004, 25, 104-106.	2.2	12
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